

Nanoscale MOS Transistors

Semi-Classical Transport and Applications

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Contents

	<i>page</i>
<i>Preface</i>	xi
<i>Acknowledgements</i>	xiv
<i>Terminology</i>	xv
1	
Introduction	1
1.1 The historical CMOS scaling scenario	1
1.2 The generalized CMOS scaling scenario	5
1.3 Support of modeling to nano-scale MOSFET design	7
1.4 An overview of subsequent chapters	9
2	
Bulk semiconductors and the semi-classical model	19
2.1 Crystalline materials	19
2.1.1 Bravaix lattice	19
2.1.2 Reciprocal lattice	21
2.1.3 Bloch functions	24
2.1.4 Density of states	29
2.2 Numerical methods for band structure calculations	30
2.2.1 The pseudo-potential method	30
2.2.2 The $\mathbf{k} \cdot \mathbf{p}$ method	34
2.3 Analytical band structure models	37
2.3.1 Conduction band	37
2.3.2 Valence band	39
2.4 Equivalent Hamiltonian and Effective Mass Approximation	41
2.4.1 The equivalent Hamiltonian	41
2.4.2 The Effective Mass Approximation	43
2.5 The semi-classical model	45
2.5.1 Wave-packets and group velocity	45
2.5.2 Carrier motion in a slowly varying potential	50
2.5.3 Carrier scattering by a rapidly fluctuating potential	54
2.5.4 The Fermi golden rule	55
2.5.5 Semi-classical electron transport	58
2.6 Summary	60

3	Quantum confined inversion layers	63
3.1	Electrons in a square well	64
3.2	Electron inversion layers	65
3.2.1	Equivalent Hamiltonian for electron inversion layers	66
3.2.2	Parabolic effective mass approximation	67
3.2.3	Implementation and computational complexity	69
3.2.4	Non-parabolic effective mass approximation	70
3.3	Hole inversion layers	72
3.3.1	$\mathbf{k}\cdot\mathbf{p}$ method in inversion layers	72
3.3.2	Implementation and computational complexity	74
3.3.3	A semi-analytical model for hole inversion layers	77
3.4	Full-band energy relation and the LCBB method	81
3.4.1	Implementation and computational complexity	84
3.4.2	Calculation results for the LCBB method	85
3.5	Sums and integrals in the \mathbf{k} space	86
3.5.1	Density of states	87
3.5.2	Electron inversion layers in the effective mass approximation	88
3.5.3	Hole inversion layers with an analytical energy model	91
3.5.4	Sums and integrals for a numerical energy model	92
3.6	Carrier densities at the equilibrium	94
3.6.1	Electron inversion layers	95
3.6.2	Hole inversion layers	97
3.6.3	Average values for energy and wave-vector at the equilibrium	98
3.7	Self-consistent calculation of the electrostatic potential	100
3.7.1	Stability issues	101
3.7.2	Electron inversion layers and boundary conditions	103
3.7.3	Speed-up of the convergence	108
3.8	Summary	108
4	Carrier scattering in silicon MOS transistors	112
4.1	Theory of the scattering rate calculations	113
4.1.1	The Fermi golden rule in inversion layers	113
4.1.2	Intra-valley transitions in electron inversion layers	114
4.1.3	Physical interpretation and validity limits of Fermi's rule	114
4.1.4	Inter-valley transitions in electron inversion layers	115
4.1.5	Hole matrix elements for a $\mathbf{k}\cdot\mathbf{p}$ Hamiltonian	123
4.1.6	A more general formulation of the Fermi golden rule	124
4.1.7	Total scattering rate	127
4.1.8	Elastic and isotropic scattering rates	127
4.2	Static screening produced by the free carriers	128
4.2.1	Basic concepts of screening	129
4.2.2	Static dielectric function for a 2D carrier gas	130
4.2.3	The scalar dielectric function	135

4.2.4	Calculation of the polarization factor	139
4.3	Scattering with Coulomb centers	143
4.3.1	Potential produced by a point charge	143
4.3.2	Scattering matrix elements	148
4.3.3	Effect of the screening	151
4.3.4	Small areas and correlation of the Coulomb centers position	153
4.4	Surface roughness scattering	156
4.4.1	Bulk n -MOSFETs	156
4.4.2	SOI n -MOSFETs	162
4.4.3	Effect of the screening in n -MOSFETs	165
4.4.4	Surface roughness in p -MOSFETs	166
4.5	Vibrations of the crystal lattice	169
4.5.1	Classical model for the lattice vibrations	169
4.5.2	Quantization of the lattice vibrations	173
4.6	Phonon scattering	176
4.6.1	Deformation potentials and scattering potentials	176
4.6.2	General formulation of the phonon matrix elements	178
4.6.3	Electron intra-valley scattering by acoustic phonons	180
4.6.4	Electron intra-valley scattering by optical phonons	187
4.6.5	Electron inter-valley phonon scattering	189
4.6.6	Hole phonon scattering	193
4.6.7	Selection rules for phonon scattering	195
4.7	Screening of a time-dependent perturbation potential	196
4.7.1	Dynamic dielectric function for a 2D carrier gas	197
4.7.2	Screening for phonon scattering	200
4.8	Summary	201
5	The Boltzmann transport equation	207
5.1	The BTE for the free-carrier gas	207
5.1.1	The BTE for electrons	208
5.1.2	The BTE for holes	211
5.2	The BTE in inversion layers	214
5.2.1	Real and wave-vector space in a 2D carrier gas	214
5.2.2	The BTE without collisions	215
5.2.3	Driving force	216
5.2.4	Scattering	219
5.2.5	Macroscopic quantities	220
5.2.6	Detailed balance at equilibrium	220
5.3	The BTE for one-dimensional systems	223
5.4	Momentum relaxation time approximation	223
5.4.1	Calculation of the momentum relaxation time	224
5.4.2	Momentum relaxation time for an electron inversion layer	229
5.4.3	Momentum relaxation time for a hole inversion layer	233

5.4.4	Calculation of mobility	235
5.4.5	Mobility for an electron inversion layer	236
5.4.6	Mobility for a hole inversion layer	239
5.4.7	Multiple scattering mechanisms and Matthiessen's rule	239
5.5	Models based on the balance equations of the BTE	241
5.5.1	Drift-Diffusion model	241
5.5.2	Analytical models for the MOSFET drain current	244
5.6	The ballistic transport regime	246
5.6.1	Carrier distribution in a ballistic MOSFET	247
5.6.2	Ballistic current in a MOSFET	250
5.6.3	Compact formulas for the ballistic current	252
5.6.4	Injection velocity and subband engineering	254
5.7	The quasi-ballistic transport regime	256
5.7.1	Compact formulas for the quasi-ballistic current	256
5.7.2	Back-scattering coefficient	259
5.7.3	Critical analysis of the quasi-ballistic model	261
5.8	Summary	263
6	The Monte Carlo method for the Boltzmann transport equation	268
6.1	Basics of the MC method for a free-electron-gas	269
6.1.1	Particle dynamics	270
6.1.2	Carrier scattering and state after scattering	273
6.1.3	Boundary conditions	279
6.1.4	Ohmic contacts	282
6.1.5	Gathering of the statistics	283
6.1.6	Enhancement of the statistics	285
6.1.7	Estimation of the current at the terminals	287
6.1.8	Full band Monte Carlo	288
6.1.9	Quantum corrections to free carrier gas MC models	290
6.2	Coupling with the Poisson equation	291
6.2.1	Poisson equation: linear and non-linear solution schemes	292
6.2.2	Boundary conditions	293
6.2.3	Charge and force assignment	293
6.2.4	Self-consistency and Coulomb interactions	296
6.2.5	Stability	296
6.3	The multi-subband Monte Carlo method	301
6.3.1	Flowchart of the self-consistent MSMC method	301
6.3.2	Free-flight, state after scattering and boundary conditions	303
6.3.3	Multi-subband Monte Carlo transport for electrons	304
6.3.4	Multi-subband Monte Carlo transport for holes	304
6.4	Summary	306
7	Simulation of bulk and SOI silicon MOSFETs	314
7.1	Low field transport	314

7.1.1	Measurement and representation of mobility data	314
7.1.2	Low field mobility in bulk devices	319
7.1.3	Low field mobility in SOI devices	324
7.2	Far from equilibrium transport	328
7.2.1	High field transport in uniform samples	329
7.2.2	High field transport in bulk and SOI devices	330
7.3	Drive current	332
7.3.1	Ballistic and quasi-ballistic transport	332
7.3.2	Voltage dependence and gate length scaling	338
7.4	Summary	341
8	MOS transistors with arbitrary crystal orientation	348
8.1	Electron inversion layers	348
8.1.1	Definitions	348
8.1.2	Subband energy and in-plane dispersion relationship	350
8.1.3	Carrier dynamics	352
8.1.4	Change of the coordinates system	353
8.1.5	Scattering rates	357
8.2	Hole inversion layers	358
8.3	Simulation results	359
8.3.1	Mobility in electron and hole inversion layers	360
8.3.2	Drain current in <i>n</i> - and <i>p</i> -MOSFETs	362
8.4	Summary	364
9	MOS transistors with strained silicon channel	366
9.1	Fabrication techniques for strain engineering	366
9.1.1	Global strain techniques	367
9.1.2	Local strain techniques	368
9.2	Elastic deformation of a cubic crystal	369
9.2.1	Stress: definitions and notation	369
9.2.2	Strain: definitions and notation	370
9.2.3	Strain and stress relation: the elastic constants	372
9.2.4	Change of coordinate systems for strain and stress	374
9.2.5	Biaxial strain	376
9.2.6	Uniaxial strain	379
9.3	Band structure in strained <i>n</i> -MOS transistors	382
9.3.1	Strain effects in the bulk silicon conduction band	383
9.3.2	Biaxial and uniaxial strain in <i>n</i> -MOS transistors	387
9.4	Band structure in strained <i>p</i> -MOS transistors	392
9.4.1	The $\mathbf{k}\cdot\mathbf{p}$ model for holes in the presence of strain	392
9.4.2	Biaxial and uniaxial strain in <i>p</i> -MOS transistors	393
9.5	Simulation results for low field mobility	394
9.6	Simulation results for drain current in MOSFETs	398
9.7	Summary	399

10	MOS transistors with alternative materials	406
10.1	Alternative gate materials	406
10.2	Remote phonon scattering due to high- κ dielectrics	407
10.2.1	Field propagation in the stack	409
10.2.2	Device structure with an infinite dielectric	411
10.2.3	Device structure with ITL/high- κ /metal-gate stack	416
10.2.4	Calculation of the scattering rates	420
10.3	Scattering due to remote Coulomb centers	423
10.3.1	Scattering matrix elements	423
10.3.2	Effect of the screening	425
10.4	Simulation results for MOSFETs with high- κ dielectrics	425
10.5	Alternative channel materials	430
10.5.1	Ballistic transport modeling of alternative channel devices	431
10.5.2	Energy reference in alternative channel materials	434
10.6	Germanium MOSFETs	435
10.6.1	Conduction band and phonon parameters	435
10.6.2	Electrons: velocity and low field mobility	437
10.6.3	Holes: band structure and low field mobility	439
10.7	Gallium arsenide MOSFETs	440
10.7.1	Conduction band parameters	440
10.7.2	Phonon scattering	441
10.7.3	Simulation results	443
10.8	Summary	444
	Appendices	451
A	Mathematical definitions and properties	451
A.1	Fourier transform	451
A.2	Fourier series	453
A.3	Fermi integrals	453
B	Integrals and transformations over a finite area A	455
C	Calculation of the equi-energy lines with the k·p model	457
C.1	Three dimensional hole gas	457
C.2	Two dimensional hole gas	458
D	Matrix elements beyond the envelope function approximation	461
E	Charge density produced by a perturbation potential	464
	<i>Index</i>	468